

### NCE N-Channel Enhancement Mode Power MOSFET

### **Description**

The NCE3404 uses advanced trench technology to provide excellent  $R_{DS(ON)}$  and low gate charge. This device is suitable for use as a load switch and PWM applications.

#### **Genera Features**

•  $V_{DS} = 30V, I_D = 5.8A$ 

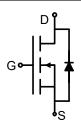
 $R_{DS(ON)}$  < 31m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)} < 43 m\Omega$  @  $V_{GS} = 4.5 V$ 

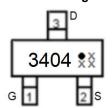
- High Power and current handing capability
- Lead free product is acquired
- Surface mount package

## **Application**

- Load switch
- ●PWM application



Schematic diagram



Marking and pin assignment



SOT-23 top view

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3404 \$₹	NCE3404	SOT-23	Ø180mm	8 mm	3000 units

### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	VDS	30	V
Gate-Source Voltage	Vgs	±20	V
Drain Current-Continuous	I <sub>D</sub>	5.8	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	20	Α
Maximum Power Dissipation	P <sub>D</sub>	1.4	W
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance,Junction-to-Ambient (Note 2)	R <sub>eJA</sub>	89	°C/W
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#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V	-	-	1	μΑ



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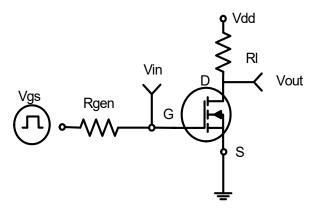
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						•
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	1.2	1.6	2.4	V
Davis Course On Otata Basistana	_	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	25.5	31	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A	-	36	43	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}=5V,I_{D}=5A$	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =15V,V <sub>GS</sub> =0V,	-	485.8	-	PF
Output Capacitance	Coss		-	65.2	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	54	-	PF
Switching Characteristics (Note 4)						•
Turn-on Delay Time	t <sub>d(on)</sub>	$V_{DD}$ =15V, $R_L$ =3 $\Omega$ $V_{GS}$ =10V, $R_{GEN}$ =3 $\Omega$	-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	3	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	15	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	3.5	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A,	-	12.6	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.9	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	2.6	-	nC
Drain-Source Diode Characteristics			'	•		•
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =5.8A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	5.8	Α

#### Notes:

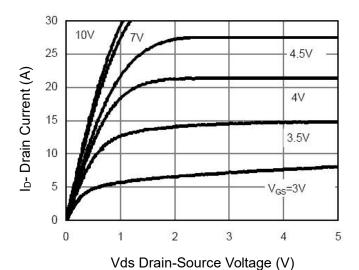
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤  $300\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



**Figure 3 Output Characteristics** 

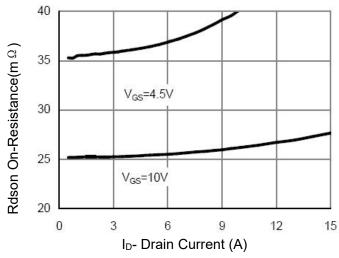
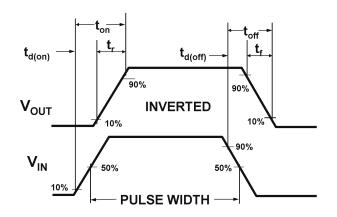


Figure 5 Drain-Source On-Resistance



**Figure 2:Switching Waveforms** 

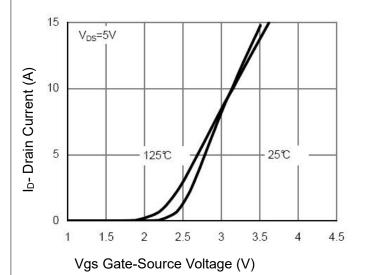


Figure 4 Transfer Characteristics

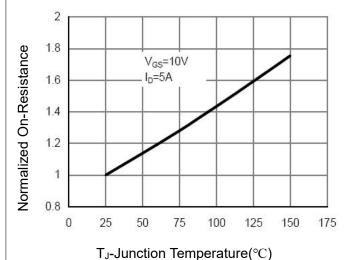
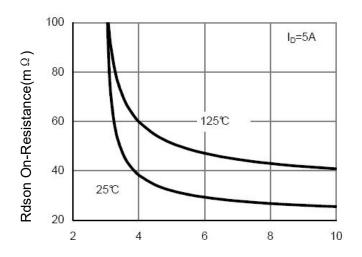


Figure 6 Drain-Source On-Resistance





Vgs Gate-Source Voltage (V) Figure7 Rdson vs Vgs

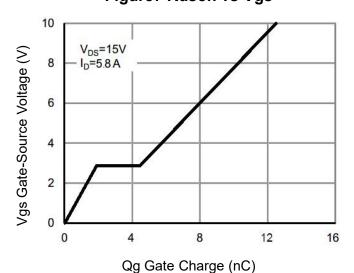


Figure 9 Gate Charge

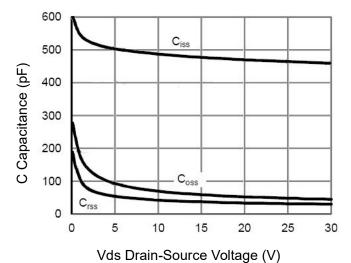
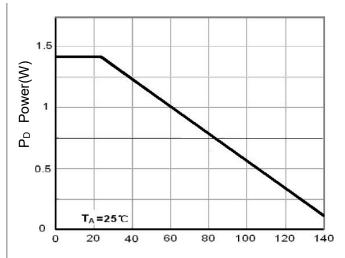


Figure 11 Capacitance vs Vds



T<sub>A</sub>-Ambient Temperature(°C) **Figure 8 Power Dissipation** 

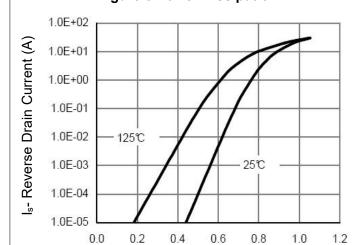
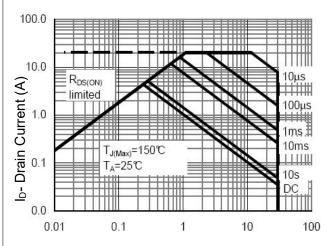


Figure 10 Source- Drain Diode Forward

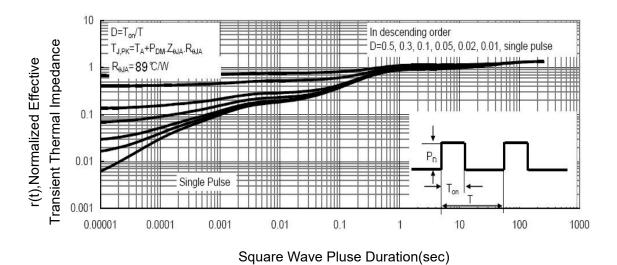
Vds Drain-Source Voltage (V)



Vds Drain-Source Voltage (V)

Figure 12 Safe Operation Area

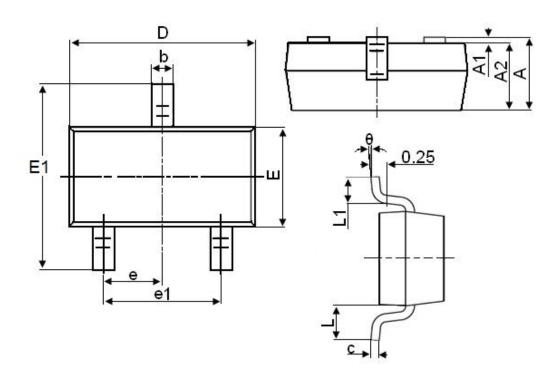




**Figure 13 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Information**



Cymphol	Dimensions in Millimeters				
Symbol	MIN.	MAX.			
А	0.900	1.150			
A1	0.000	0.100			
A2	0.900	1.050			
b	0.300	0.500			
С	0.080	0.150			
D	2.800	3.000			
Е	1.200	1.400			
E1	2.250	2.550			
е		0.950TYP			
e1	1.800	2.000			
L		0.550REF			
L1	0.300	0.500			
θ	0°	8°			

#### Notes

- 1. All dimensions are in millimeters.
- 2. Tolerance ±0.10mm (4 mil) unless otherwise specified
- 3. Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- 4. Dimension L is measured in gauge plane.
- 5. Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.



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